

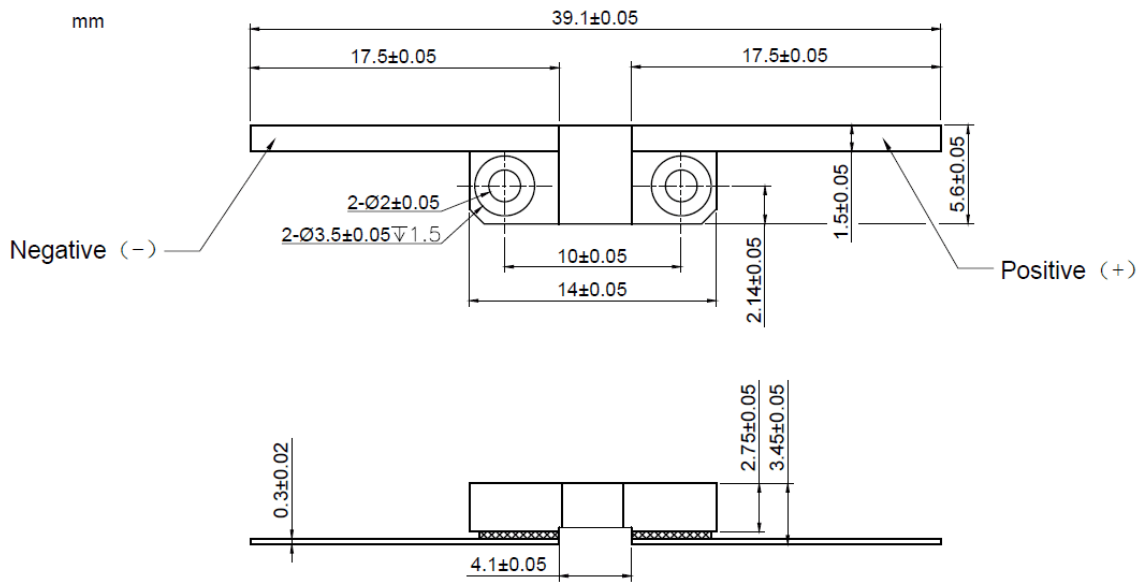
660nm 1W High Power Laser Diode| E-mount Package| High Power Red LD| FAC Optional

658nm~660nm 1W E-mount Diode Laser | Red Laser Diodes

RWSLD-660-001-E

660nm Laser Diode		1W/E-mount	
PARAMETER	SYMBOL	VALUE	UNIT
Reverse Voltage	V_r	2.0	V
Operating Temperature	T_{op}	+10~+30	°C
Storage Temperature	T_{stg}	-20~ +80	°C
Lead soldering temperature (10 sec.)	T_{is}	260	°C
Features: <ul style="list-style-type: none"> ● 660nm ● High Power ,CW, Multi-mode ● High Quality ● E-mount Package 			
Applications: <ul style="list-style-type: none"> ● Medical Laser Treatment ● Laser Indicator ● Laser Detector 			
Specifications		RWSLD-660-001-E	
		Min	Type
			Max
Center Wavelength@25°C		660nm ± 10nm	
Spectral Width (FWHM)		2nm	
Output Power		1W	
Emitter Area		100x1µm	
Beam Divergence (FWHM)		35° _⊥ x 8° _{//}	
Temperature Coefficient of Wavelength		0.2nm / °C	
Slope Efficiency		1.1W/A	
Threshold Current (Typ.)		0.5A	
Operating Current (Typ.)		1.5A	
Operating Voltage		2.4V	
Package Style		E-mount	
Recommended Operation Temp		25°C	

E-mount Package View:



**Electrically shorten LD module and store in non-extreme conditions.
Suggest using the constant current power supply.**

